

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-57. (cancelled).

58. (currently amended) A method of manufacturing a semiconductor device, comprising the steps of:

(a) providing a tape having a main surface, a back surface opposed to the main surface, a product forming portion formed on the main surface, and a plurality of terminals formed in the product forming portion;

(b) fixing a semiconductor element to the main surface of the tape;

(c) electrically connecting a plurality of electrodes formed over the semiconductor element with the plurality of terminals through wires, respectively;

(d) sealing the semiconductor element, the wires, the plurality of terminals and the main surface of the tape with a resin, and forming a sealing member;

(e) after the step (d), peeling the tape from the sealing member, and thereby exposing a part of each of the plurality of terminals from the sealing member; and

(f) forming a metal layer over the exposed part of each of the plurality of terminals,

wherein there is no exposure of the plurality of terminals and terminal leads ~~from~~ at outer edges of the sealing member; and

wherein the metal layer is formed by a printing process.

59. (previously presented) The method according to claim 58, wherein the plurality of terminals are formed by affixing a metal foil to the main surface of the tape and thereafter etching the metal foil selectively.

60. (previously presented) The method according to claim 59, wherein the metal foil is affixed to the main surface of the tape through a first adhesive.

61. (previously presented) The method according to claim 59, wherein the metal foil is compression-bonded to the tape by thermocompression bonding.

62. (previously presented) The method according to claim 58, wherein a back surface of the semiconductor element is exposed from the sealing member.

63. (previously presented) The method according to claim 58, wherein the tape has a semiconductor element fixing piece, and the semiconductor element is mounted over the semiconductor element fixing piece.

64. (previously presented) The method according to claim 58, wherein the plurality of terminals are fixed to the tape through a first adhesive, and the semiconductor element is fixed to the tape through a second adhesive.

65. (previously presented) The method according to claim 59, wherein a Pd plating film is formed over each of the plurality of terminals.

66. (previously presented) The method according to claim 58, wherein the tape is formed by a resin film selected from polyimide resin, ethylene-vinylacetate copolymer resin, polyolefin resin and methacrylate resin.

67. (previously presented) The method according to claim 58, wherein the step (d) is carried out while the back surface of the tape is held by vacuum suction.

68. (new) A method of manufacturing a semiconductor device, comprising the steps of:

(a) providing a tape having a main surface, a back surface opposed to the main surface, a product forming portion formed on the main surface, and a plurality of terminals formed in the product forming portion;

(b) fixing a semiconductor element to the main surface of the tape;

(c) electrically connecting a plurality of electrodes formed over the semiconductor element with the plurality of terminals through wires respectively;

(d) sealing the semiconductor element, the wires, the plurality of terminals and the main surface of the tape with a resin, and forming a sealing member;

(e) after the step of (d), peeling the tape from the sealing member, and thereby exposing a part of each of the plurality of terminals from the sealing member; and

(f) forming a metal layer over the exposed part of each of the plurality of terminals,

wherein there is no exposure of the plurality of terminals and terminal leads at side edges of the sealing member; and

wherein the metal layer is formed by a printing process.

69. (new) The method according to claim 68, wherein the plurality of terminals are formed by affixing a metal foil to the main surface of the tape and thereafter etching the metal foil selectively.

70. (new) The method according to claim 69, wherein the metal foil is affixed to the main surface of the tape through a first adhesive.

71. (new) The method according to claim 69, wherein the metal foil is compression-bonded to the tape by thermocompression bonding.

72. (new) The method according to claim 68, wherein a back surface of the semiconductor element is exposed from the sealing member.

73. (new) The method according to claim 68, wherein the tape has a semiconductor element fixing piece, and the semiconductor element is mounted over the semiconductor element fixing piece.

74. (new) The method according to claim 68, wherein the plurality of terminals are fixed to the tape through a first adhesive, and the semiconductor element is fixed to the tape through a second adhesive.

75. (new) The method according to claim 69, wherein a Pd plating film is formed over each of the plurality of terminals.

76. (new) The method according to claim 68, wherein the tape is formed by a resin film selected from polyimide resin, ethylene-vinylacetate copolymer resin, polyolefin resin and methacrylate resin.

77. (new) The method according to claim 68, wherein the step (d) is carried out while the back surface of the tape is held by vacuum suction.

78. (new) A method of manufacturing a semiconductor device, comprising the steps of:

(a) providing a tape having a main surface, a back surface opposed to the main surface, a product forming portion formed on the main surface, and a plurality of terminals formed in the product forming portion;

(b) fixing a semiconductor element to the main surface of the tape;

(c) electrically connecting a plurality of electrodes formed over the semiconductor element with the plurality of terminals through wires respectively;

(d) sealing the semiconductor element, the wires, the plurality of terminals and the main surface of the tape with a resin, and forming a sealing member;

(e) after the step of (d), peeling the tape from the sealing member, and thereby exposing a part of each of the plurality of terminals from the sealing member; and

(f) forming a metal layer over the exposed part of each of the plurality of terminals,

wherein the plurality of terminals and terminal leads are exposed from only a bottom surface of the sealing member; and

wherein the metal layer is formed by a printing process.

79. (new) The method according to claim 78, wherein the plurality of terminals are formed by affixing a metal foil to the main surface of the tape and thereafter etching the metal foil selectively.

80. (new) The method according to claim 79, wherein the metal foil is affixed to the main surface of the tape through a first adhesive.

81. (new) The method according to claim 79, wherein the metal foil is compression-bonded to the tape by thermocompression bonding.

82. (new) The method according to claim 78, wherein a back surface of the semiconductor element is exposed from the sealing member.

83. (new) The method according to claim 78, wherein the tape has a semiconductor element fixing piece, and the semiconductor element is mounted over the semiconductor element fixing piece.

84. (new) The method according to claim 78, wherein the plurality of terminals are fixed to the tape through a first adhesive, and the semiconductor element is fixed to the tape through a second adhesive.



85. (new) The method according to claim 79, wherein a Pd plating film is formed over each of the plurality of terminals.

86. (new) The method according to claim 78, wherein the tape is formed by a resin film selected from polyimide resin, ethylene-vinylacetate copolymer resin, polyolefin resin and methacrylate resin.

87. (new) The method according to claim 78, wherein the step (d) is carried out while the back surface of the tape is held by vacuum suction.